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## FAX COVER SHEET

DATE: October 28, 2011

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OPERATOR: \_\_\_\_\_ TIME COMPLETED: \_\_\_\_\_  
PLEASE CALL (202) 263-4300 IF YOU HAVE ANY PROBLEMS

## MESSAGE:

Re: U. S. Patent Application No. 10/591,476

Dear Ms. Louie:

Attached is a copy of our proposed amendments to claims 8 and 9 that we will discuss during our interview on November 2, 2011 at 1:30 p.m.

Michael A. Makuch

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## CONFIDENTIALITY NOTE:

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**PROPOSED AMENDMENTS TO CLAIMS 8 AND 9**  
**(U.S. Patent Application No. 10/591,476)**

8. (Proposed Amendments) A film deposition method that alternately performs a step of supplying a Cu-containing source material onto a substrate and a step of supplying a reductive gas to the substrate after stopping supplying the Cu-containing source material, wherein said method has:

a first film deposition period in an early deposition stage in which the two steps are performed alternately, each of the two steps is performed two or more times in the first film deposition period, and each of the steps of supplying the reductive gas is performed for a first period of time T1; and

a second film deposition period following the first film deposition period in which the two steps are performed alternately, each of the two steps is performed two or more times in the second film deposition period, and each of the steps of supplying the reductive gas is performed for a second period of time T2 shorter than the period of time T1.

9. (Proposed Amendments) A film deposition method comprising the steps of:

placing a substrate in a process container; and repeating the following steps (a) to (d):

(a) supplying a Cu-containing source material onto the substrate;

(b) removing residual gases in the process container therefrom after stopping supplying the Cu-containing source material;

(c) supplying a reductive gas to the substrate; and

(d) removing residual gases in the process container therefrom after stopping supplying the reductive gas,

wherein said method has:

a first film deposition period in an early deposition stage in which the steps (a) to (d) are performed alternately, each of the steps (a) to (d) is performed two or more times in the first film deposition period, and each of the steps of supplying the reductive gas is performed for a first period of time T1; and

a second film deposition period following the first film deposition period in which the steps (a) to (d) are performed alternately, each of the steps (a) to (d) is performed two or more times in the second film deposition period, and each of the steps of supplying the reductive gas is performed for a second period of time T2 shorter than the period of time T1.